Dual N-Channel 30V (D-S) MOSFET

CHARACTERISTICS

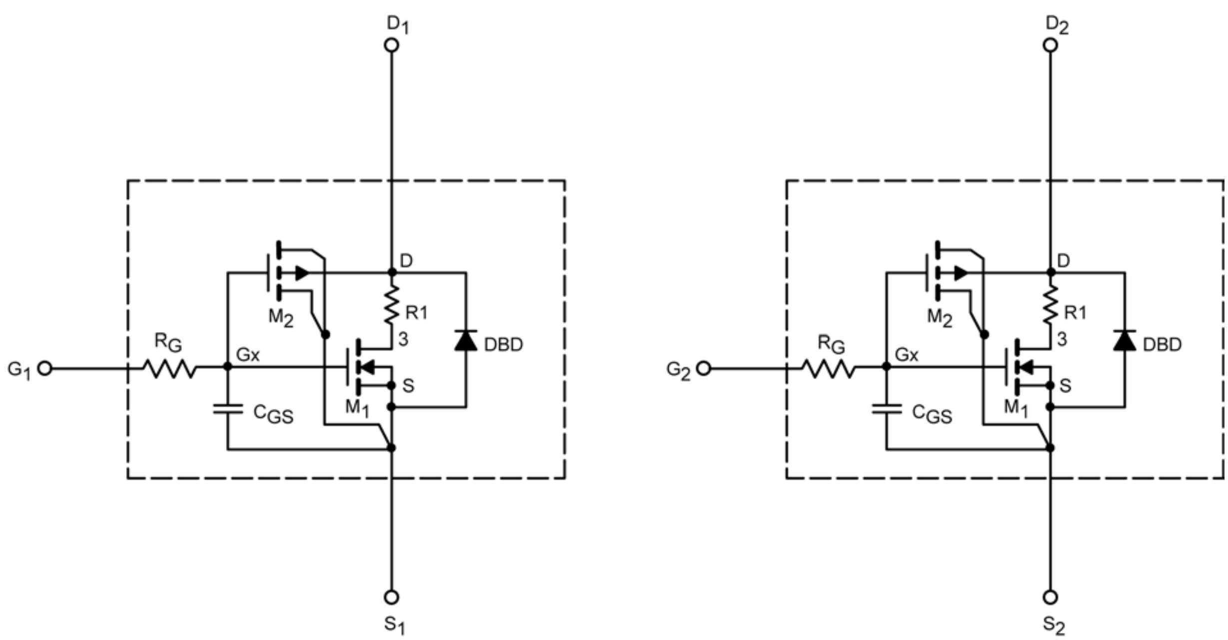
- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the −55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

DESCRIPTION

The attached spice model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the −55 to 125°C temperature ranges under the pulsed 0-V to 10-V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC

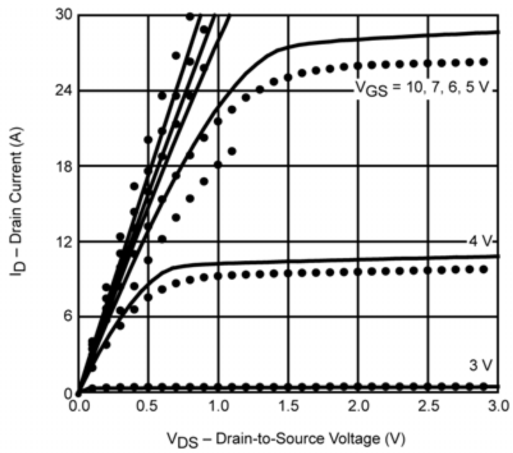


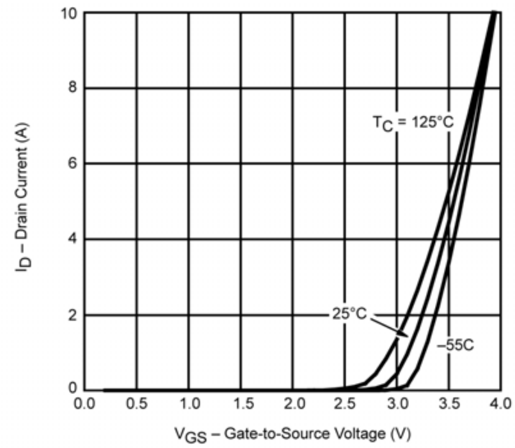
This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

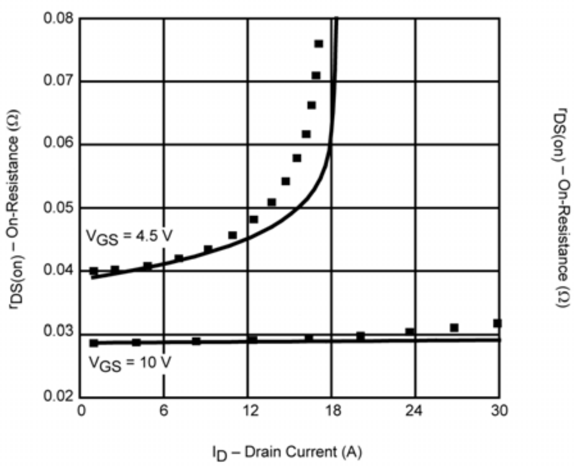
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)					
Parameter	**Symbol**	**Test Condition**	**Simulated Data**	**Measured Data**	**Unit**
Static					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250 µA	2.2		V
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq 5$ V, V_{GS} = 10 V	153		A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 5.9 A	0.029	0.029	Ω
		V_{GS} = 4.5 V, I_D = 4.9 A	0.041	0.042	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 5.9 A	12	12	S
Forward Voltage[a]	V_{SD}	I_F = 4.7 A	0.81	0.80	V
Dynamic[b]					
Input Capacitance	C_{iss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz	545	530	pF
Output Capacitance	C_{oss}		97	100	
Reverse Transfer Capacitance	C_{rss}		44	55	
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 10 V, I_D = 5.9 A	8.3	9.1	nC
		V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 5.9 A	4.2	4.5	
Gate-Source Charge	Q_{gs}		1.8	1.8	
Gate-Drain Charge	Q_{gd}		1.7	1.7	

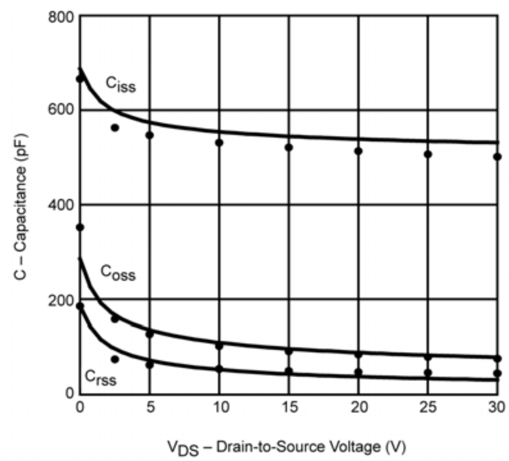
Notes
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

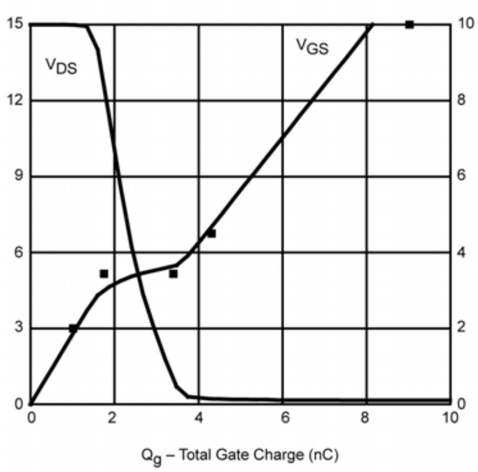
COMPARISON OF MODEL WITH MEASURED DATA (T_J=25°C UNLESS OTHERWISE NOTED)

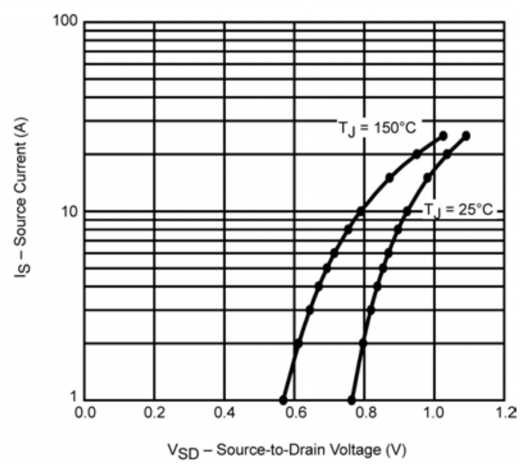












Note: Dots and squares represent measured data.

Disclaimer

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